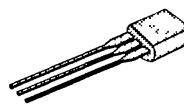


PRODUCT SUMMARY

PART NUMBER	$V_{(BR)DSS}$ (V)	$r_{DS(ON)}$ (Ω)	I_D (A)	PACKAGE
VN0603L	60	3.5	0.30	TO-92
VN0603T	60	3.5	0.22	SOT-23

Performance Curves: VNDS06 (See Section 7)

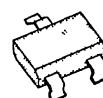
TO-92



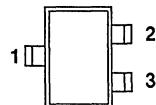
BOTTOM VIEW


 1 SOURCE
 2 GATE
 3 DRAIN

SOT-23



TOP VIEW


 1 DRAIN
 2 SOURCE
 3 GATE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETERS/TEST CONDITIONS	SYMBOL	VN0603L	VN0603T	UNITS
Drain-Source Voltage	V_{DS}	60	60	V
Gate-Source Voltage	V_{GS}	± 30	± 30	
Continuous Drain Current	I_D	0.30	0.22	A
		0.21	0.14	
Pulsed Drain Current ¹	I_{DM}	1	0.8	W
Power Dissipation	P_D	0.8	0.36	
		0.32	0.14	
Operating Junction and Storage Temperature	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$
Lead Temperature (1/16" from case for 10 seconds)	T_L	300		

THERMAL RESISTANCE

THERMAL RESISTANCE	SYMBOL	VN0603L	VN0603T	UNITS
Junction-to-Ambient	R_{thJA}	156	350	$^\circ\text{C}/\text{W}$

¹Pulse width limited by maximum junction temperature

VN0603 SERIES

Siliconix
incorporated

ELECTRICAL CHARACTERISTICS ¹			LIMITS					
PARAMETER	SYMBOL	TEST CONDITIONS	TYP ²	VN0603L		VN0603T		UNIT
				MIN	MAX	MIN	MAX	
STATIC								
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 \text{ V}, I_D = 10 \mu\text{A}$	70	60		60		V
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 1 \text{ mA}$	2.3	0.8	3	0.8	3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	± 1		± 100		± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48 \text{ V}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$	0.02		1		1	μA
On-State Drain Current ³	$I_{D(\text{ON})}$	$V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}$	1000	750		500		mA
Drain-Source On-Resistance ³	$r_{DS(\text{ON})}$	$V_{GS} = 4.5 \text{ V}, I_D = 50 \text{ mA}$	4.5		7.5		7.5	Ω
		$V_{GS} = 10 \text{ V}$ $I_D = 0.2 \text{ A}$ $T_J = 125^\circ\text{C}$	2.5		3.5		3.5	
Forward Transconductance ³	g_{FS}	$V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ A}$ VN0603L	230	100		100		mS
		$V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ A}$ VN0603T	230	100		100		
Common Source Output Conductance ³	g_{OS}	$V_{DS} = 10 \text{ V}, I_D = 50 \text{ mA}$	500					μs
DYNAMIC								
Input Capacitance	C_{iss}	$V_{DS} = 25 \text{ V}$ $V_{GS} = 0 \text{ V}$ $f = 1 \text{ MHz}$	16		60		60	pF
Output Capacitance	C_{oss}		11		40		40	
Reverse Transfer Capacitance	C_{rss}		2		10		10	
SWITCHING								
Turn-On Time	t_{ON}	$V_{DD} = 15 \text{ V}, R_L = 23 \Omega$ $I_D = 0.2 \text{ A}, V_{GEN} = 10 \text{ V}$ $R_G = 25 \Omega$ (Switching time is essentially independent of operating temperature)	10		15		15	ns
Turn-Off Time	t_{OFF}		10		15		15	

- NOTES: 1. $T_A = 25^\circ\text{C}$ unless otherwise noted.
 2. For design aid only, not subject to production testing.
 3. Pulse test; $PW = 300 \mu\text{s}$, duty cycle $\leq 2\%$.